



**SANYO Semiconductors**

# DATA SHEET

An ON Semiconductor Company

## STK621-033N-E — Thick-Film Hybrid IC 3-phase Inverter Motor Drive Inverter Hybrid IC

### Overview

This IC is a 3-phase inverter power hybrid IC containing power elements (IGBT and FRD), pre-driver, as well as protection circuit in one package.

### Application

- 3-phase inverter motor drive

### Features

- Integrates power elements (IGBT and FRD), pre-driver, and protective circuit.
- Protective circuits including overcurrent (bus line), pre-drive low voltage protection are built in.
- Direct input of CMOS level control signals without an insulating circuit (photocoupler, etc) is possible.
- Built-in simultaneous upper/lower ON prevention circuit to prevent arm shorting through simultaneous ON input for the upper and lower side transistors.  
(Dead time is required for preventing shorting due to switching delay.)
- The level of the overcurrent protection current is programmable with the external resistance RSD between the ISD and V<sub>SS</sub> terminals. (It is necessary to connect RSD to ensure normal operation of the overcurrent protection function.  
ISD = 21A to 28A when RSD = 0Ω)
- SIP (The single in-line package) of the transfer full mold structure.

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# STK621-033N-E

## Specifications

### Absolute Maximum Ratings at $T_c = 25^\circ\text{C}$

Parameter	Symbol	Conditions	Ratings	unit
Supply voltage	$V_{CC}$	+ - -, surge < 500V *1	450	V
Collector-emitter voltage	$V_{CE}$	+ - U (V, W) or U (V, W) - -	600	V
Output current	$I_O$	+, -, U, V, W terminal current	$\pm 15$	A
Output peak current	$I_{op}$	+, -, U, V, W terminal current $PW = 100\mu\text{s}$	$\pm 30$	A
Pre-driver supply voltage	VD1, 2, 3, 4	VB1 - U, VB2 - V, VB3 - W, $V_{DD} - V_{SS}$ *2	20	V
Input signal voltage	$V_{IN}$	HIN1, 2, 3, LIN1, 2, 3 terminal	0 to 7	V
FAULT terminal voltage	VFAULT	FAULT terminal	20	V
Maximum loss	$P_d$	Per 1 channel	24	W
Junction temperature	$T_j$	IGBT, FRD junction temperature	150	$^\circ\text{C}$
Storage temperature	$T_{stg}$		-40 to +125	$^\circ\text{C}$
Operating temperature	TC	H-IC case temperature	-20 to +100	$^\circ\text{C}$
Tightening torque		A screw part at use M3 type screw *3	1.0	N•m
Withstand voltage	Vis	50Hz sine wave AC 1 minute *4	2000	VRMS

In the case without the instruction, the voltage standard is - terminal =  $V_{SS}$  terminal voltage.

\*1 Surge voltage developed by the switching operation due to the wiring inductance between the + and - terminals.

\*2 VD1 = between VB1-U, VD2 = VB2-V, VD3 = VB3-W, VB4 =  $V_{DD} - V_{SS}$ , terminal voltage.

\*3 Flatness of the heat-sink should be lower than 0.15mm.

\*4 The test condition is AC 2500V, 1 second.

### Electrical Characteristics at $T_c=25^\circ\text{C}$ , $V_D=15\text{V}$

Parameter	Symbol	Conditions	Test Circuit	Ratings			unit	
				min	typ	max		
Power output part								
Collector-to-emitter cut-off current	$I_{CE}$	$V_{CE} = 600\text{V}$	Fig.1			0.5	mA	
Collector-to-emitter saturation voltage	$V_{CE(SAT)}$	$I_O = 15\text{A}$	Upper side	Fig.2		2.2	2.9	V
			Lower side			2.6	3.3	V
Diode forward voltage	$V_F$	$I_O = -15\text{A}$	Upper side	Fig.3		1.9	2.7	V
			Lower side			2.2	3.0	V
Junction-to-substrate thermal resistance	$\theta_{j-c}(T)$	IGBT				5.0	$^\circ\text{C/W}$	
	$\theta_{j-c}(D)$	FWD				7.3	$^\circ\text{C/W}$	
Control (Pre-driver) part								
Pre-drive power supply consumption electric current	$I_D$	VD1, 2, 3 = 15V	Fig.4		0.07	0.4	mA	
		VD4 = 15V			3.5	7		
Input ON voltage	$V_{IH}$	Output ON				0.8	V	
Input OFF voltage	$V_{IL}$	Output OFF		3.0			V	
Protection part								
Over-current protection electric current	ISD	$PW = 100\mu\text{s}$ , $R_{DS} = 0\Omega$	Fig.5	21		28	A	
Pre-drive low voltage protection	UVLO			10		12	V	
Fault terminal input electric current	IOSD	$V_{Fault} = 0.1\text{V}$			2.0		mA	
Fault clearness delay time	FLTCLR	After each protection operation ending		18		80	ms	
Switching time								
Switching time	$t_{ON}$	$I_O = 15\text{A}$ , Inductive load	Fig.6		0.7		$\mu\text{s}$	
	$t_{OFF}$				1.2		$\mu\text{s}$	
Electric current output signal level	ISO	$I_O = 15\text{A}$			0.45		V	

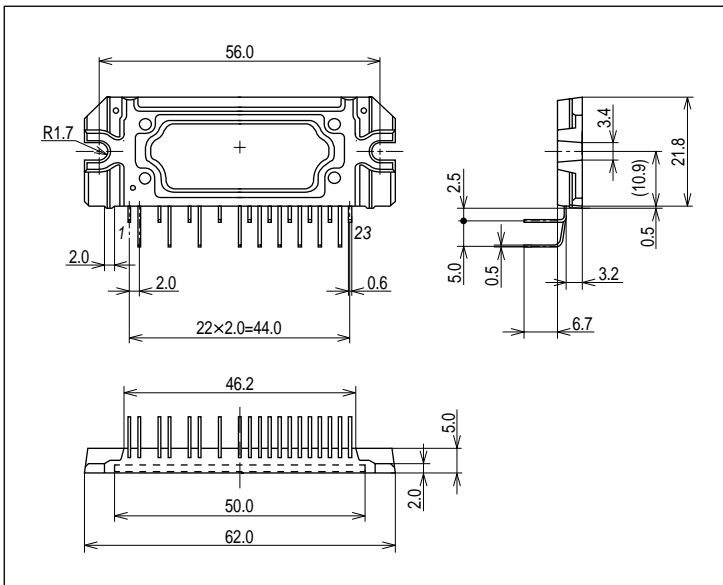
In the case without the instruction, the voltage standard is - terminal =  $V_{SS}$  terminal voltage.

## Notes

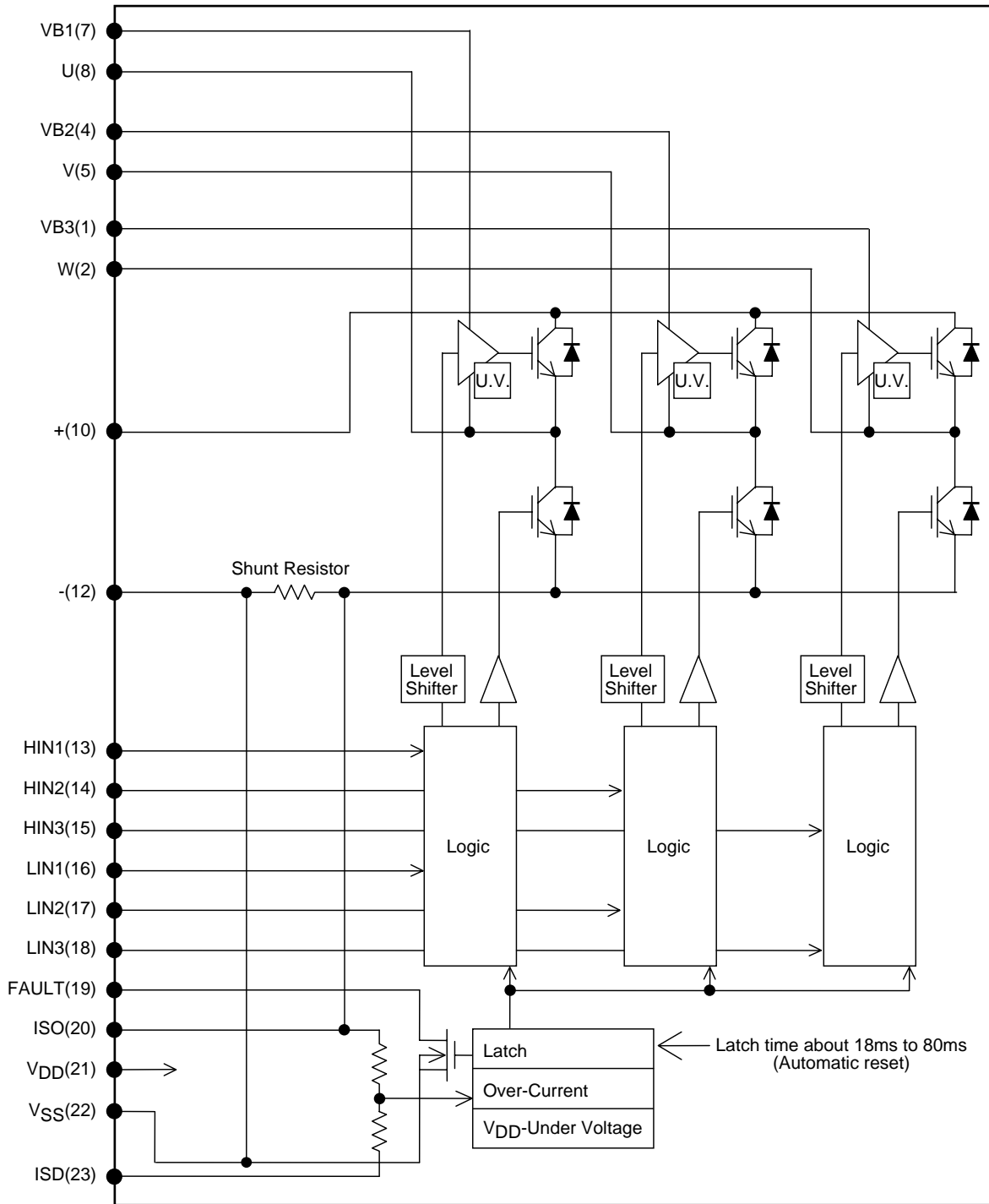
1. Input ON voltage indicates a value to turn on output stage IGBT.  
 Input OFF voltage indicates a value to turn off output stage IGBT.  
 At the time of output ON, set the input signal voltage 0V to  $V_{IH}$  (MAX).  
 At the time of output OFF, set the input signal voltage  $V_{IL}$  (MIN) to 5V.
2. When the internal protection circuit operates, there is a Fault signal ON (When the Fault terminal is low level, Fault signal is ON state : output form is open DRAIN) but the Fault signal doesn't latch.  
 After protection operation ends, it returns automatically within about 18ms to 80ms and resumes operation beginning condition. So, after Fault signal detection, set OFF (HIGH) to all input signals at once.  
 However, the operation of pre-drive power supply low voltage protection (UVLO: it has a hysteresis about 0.3V) is as follows.  
 Upper side → There is no Fault signal output, but it does a corresponding gate signal OFF.  
     Incidentally, it returns to the regular operation when recovering to the normal voltage, but the latch continues among input signal ON (LOW).  
 Lower side → It outputs Fault signal with gate signal OFF.  
     However, it is different from the protection operation of upper side, it is automatically resets about 18ms to 80ms later and resumes operation beginning condition when recovering to normal voltage.  
     (The protection operation doesn't latch by the input signal.)
3. When assembling the hybrid IC on the heat sink with M3 type screw, tightening torque range is 0.8N•m to 1.0N•m.  
 Flatness of the heat-sink should be lower than 0.15mm.
4. The pre-drive low voltage protection is the feature to protect a device when the pre-driver supply voltage declines with the operating malfunction. As for the pre-driver supply voltage decline in case of operation beginning, and so on, we request confirmation in the set.

## Package Dimensions

unit:mm (typ)



Internal Equivalent Circuit Diagram



**Test Circuit**

(The tested phase : U+ shows the upper side of the U phase and U- shows the lower side of the U phase.)

Fig 1:  $I_{CE}$

	U+	V+	W+	U-	V-	W-
M	10	10	10	8	5	2
N	8	5	2	12	12	12

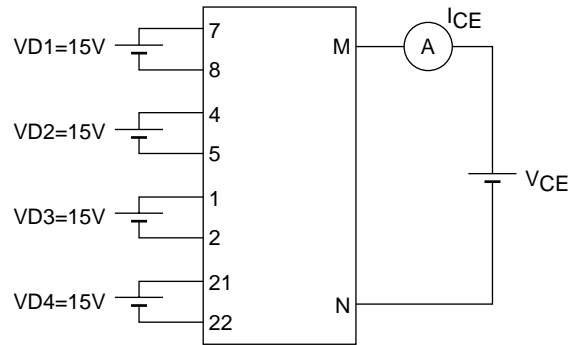


Fig 2:  $V_{CE(SAT)}$

	U+	V+	W+	U-	V-	W-
M	10	10	10	8	5	2
N	8	5	2	12	12	12
m	13	14	15	16	17	18

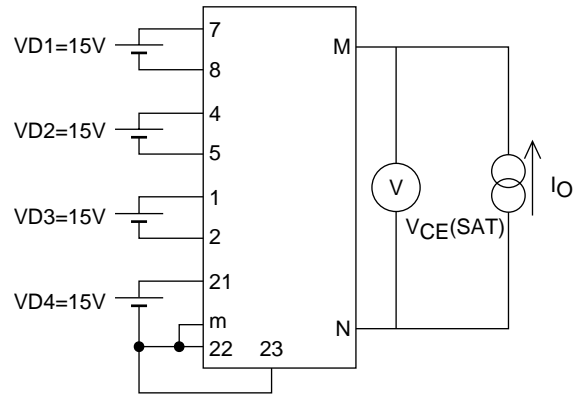


Fig 3:  $V_F$

	U+	V+	W+	U-	V-	W-
M	10	10	10	8	5	2
N	8	5	2	12	12	12

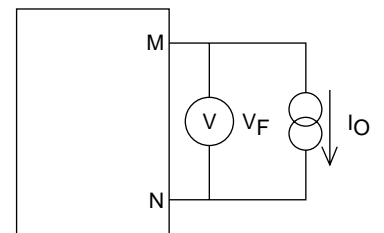


Fig 4:  $I_D$

	VD1	VD2	VD3	VD4
m	7	4	1	21
n	8	5	2	22

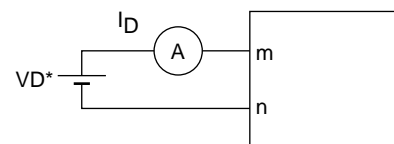


Fig 5: ISD

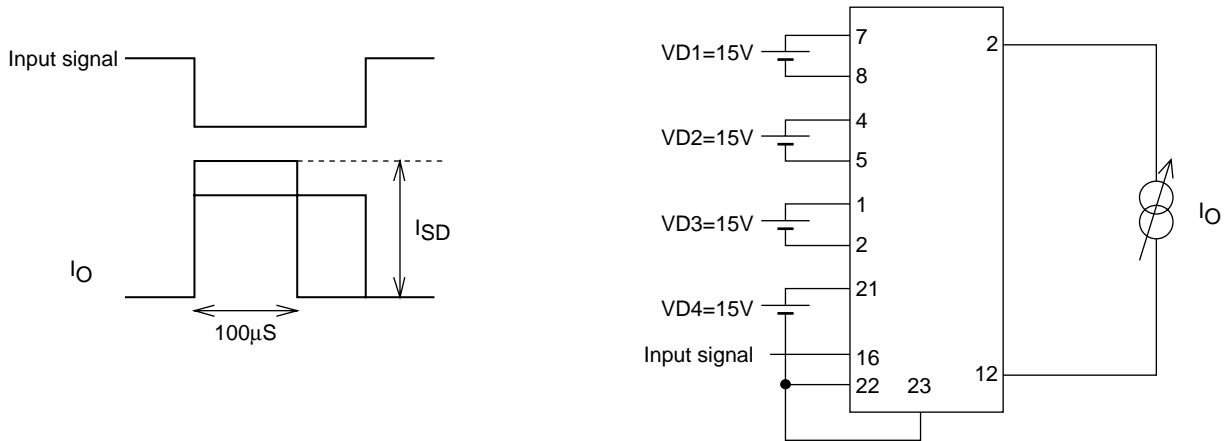
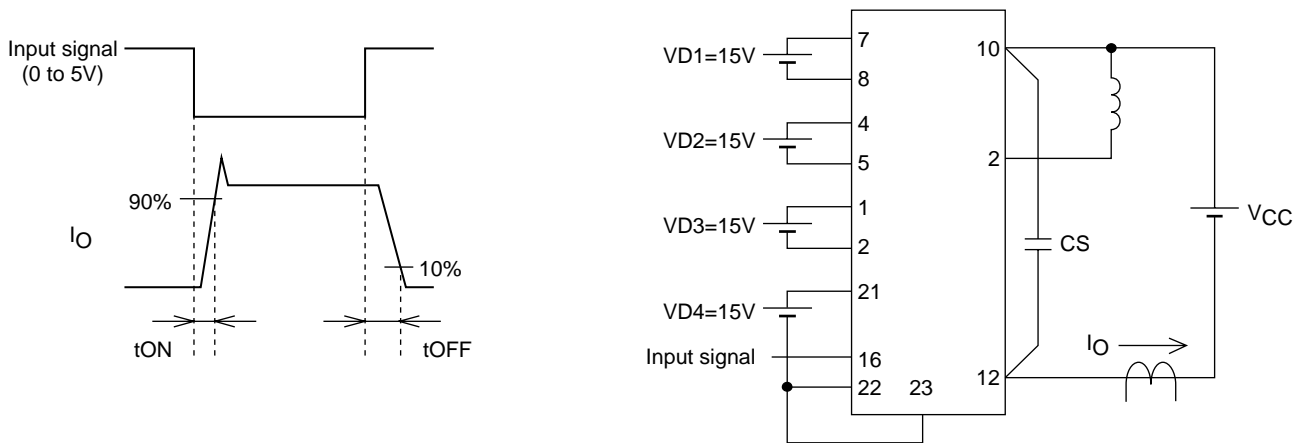
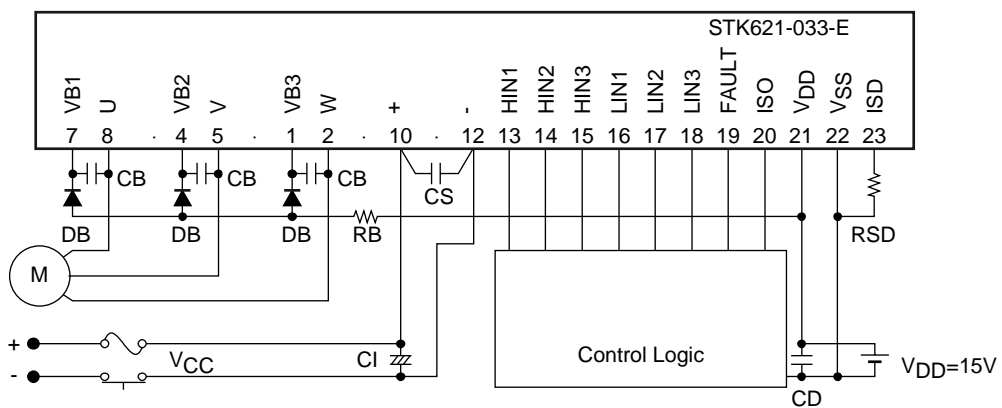


Fig 6: Switching Time



Example of the application circuit



**Recommendation Operating Conditions**

Parameter	Symbol	Conditions	min	typ	max	unit
Supply voltage	V <sub>CC</sub>	+ - -	0	280	400	V
Pre-driver supply voltage	VD1, 2, 3	VB1 - U, VB2 - V, VB3 - W	12.5	15	17.5	V
	VD4	V <sub>DD</sub> - V <sub>SS</sub> *1	13.5	15	16.5	
Input ON voltage	V <sub>IN(ON)</sub>	HIN1, HIN2, HIN3,	0		0.3	V
Input OFF voltage	V <sub>IN(OFF)</sub>	LIN1, LIN2, LIN3 Terminal				
PWM frequency	f <sub>PWM</sub>		1		10	kHz
Dead time	DT	Upper/lower input signal downtime	2			μs
Tightening torque	MT	'M3' Type Screw	0.8		1.0	N•m

\*1. Pre-driver power supply (VD4 = 15±1.5V) must have the capacity of I<sub>O</sub> = 20mA (DC), 0.5A (Peak).

**Usage Precaution**

- By the addition of the diode for the bootstrap (DB : high speed type of trr 100ns or less, withstand voltage equal to or more than 600V) and of the capacitor (CB : about 1 to 47μF), a single power supply drive is enabled. In this case, it makes a lower side IGBT ON (input signal of lower side makes LOW).  
Then it charges in CB. Incidentally, in case of start-up and so, when the voltage of CB is low, the big charging electric current flows and sometimes becomes the cause which exerts a bad influence of noise and so on. Put limitation resistor RB (Several Ω to about tens of Ω).  
(When not using the bootstrap circuit, each upper side pre-drive power supply needs an external independent power supply.)  
Also, the upper side power supply voltage sometimes declines by the way of controlling. Please confirm.
- Because the jump voltage which is accompanied by the vibration in case of switching operation occurs by the influence of the floating inductance of the wiring of the outer power supply which is connected with of the + terminal and the - terminal, restrains and spares surge voltage being as the connection of the snubber circuit (Capacitor/CS/about 0.22 - 10μF) for the voltage absorption with the neighborhood as possible between + and the - terminal, and so on, with making a wiring length (among the terminals each from CI) short and making a wiring inductance small.
- ISO terminal (20pin) is for the electric current monitor. When the pull up with the resistance, use above 5.6kΩ Be careful, because the overcurrent protection does not operate when short-circuiting in the ISO terminal and the V<sub>SS</sub> terminal.
- Output form of the FAULT terminal is open DRAIN (it is operating as FAULT when becoming LOW).  
When the pull up with the resistance, use above 5.6kΩ.
- Zener diode with 5V (5.0 - 5.4V) is connected with the inside of the signal input terminal. When inputting the voltage which exceeds 5V, connect resistor to between the side of the power and the signal input terminal, for the input current of the signal input terminal become equal to or less than 0.5mA.  
This resistor is effective with the noise absorption of the signal terminal, too.
- The overcurrent protection feature operates only when it is possible to do a circuit control normally. For the safety, put a fuse, and so on in the V<sub>CC</sub> line.
- Because the IC sometimes destroys and bursts when motor connection terminal (2pin, 5pin, 8pin) becomes open while the motor turns, especially, be careful of the connection ( the soldering condition ) of this terminal.
- The over current protection feature operates normally when an external resistor RSD is connected between the ISD and V<sub>SS</sub> terminals. Be sure to connect this resistor. The Level of the overcurrent protection current is variable according to the RSD value. Select an RSD resistor of an optimum value while referring to the formula shown on a separate sheet and connect it between the ISD and V<sub>SS</sub> terminals.
- If - terminal and V<sub>SS</sub> terminal are short-circuited, since an over-current protection (ISD) value will become lower than the inside setting value of HIC, please do not connect externally.  
(-terminal and V<sub>SS</sub> terminal are connected inside HIC)

This data shows the example of the application circuit, does not guarantee a design as the mass production set.

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